Introduction

The behavior of a semiconductor device depends on the temperature of its silicon chip. This is why electrical parameters are given at a specified temperature.

To sustain the performance of a component and to avoid failure, the temperature has to be limited by managing the heat transfer between the chip and the ambient atmosphere. The aim of this note is to show how to calculate a suitable heatsink for a semiconductor device and the precautions needed for handling, mounting and soldering techniques.
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1 Through-hole packages

1.1 Thermal resistance

1.1.1 Review

The thermal resistance of semiconductor assembly is the parameter which characterizes its resistance to the heatflow generated by the junction during operation. A temperature exceeding the maximum junction temperature curtails the electrical performance and may damage the device.

The maximum dissipated power capability is:

\[ P_{\text{max}} = \frac{T_{\text{j},\text{max}} - T_a}{R_{\text{th}(j-a)}} \]

Where:
- \( T_{\text{j},\text{max}} \) is the maximum junction temperature of the semiconductor in degrees (°C)
- \( T_a \) is the ambient air temperature in degrees (°C)
- \( R_{\text{th}(j-a)} \) is the thermal resistance between junction and ambient air in °C/W

The \( R_{\text{th}(j-a)} \) takes into account all materials between the junction and ambient air.

An analogy between Ohm’s law and the thermal equivalent circuit can be made:
- Electrical resistance corresponds to thermal resistance
- Current corresponds to dissipated power
- Voltage corresponds to temperature

Thus: \( V = R \cdot I \) corresponds to \( \Delta T = R_{\text{th}} \cdot P \)

1.1.2 Dissipated power for a thyristor or a TRIAC

The maximum power dissipation versus average on-state current (for SCRs) or RMS on-state current (for TRIACs) is given in the datasheet for each product.

However, a more accurate result is obtained by using the \( V_{\text{to}} \) and \( R_d \) values with the following calculation:

\[ P = V_{\text{to}} \cdot I_{\text{T}(AV)} + R_d \cdot I_{\text{T}(RMS)}^2 \]

Where:
- \( V_{\text{to}} \) is the threshold voltage specified in the datasheet
- \( R_d \) is the dynamic on-state resistance specified as \( R_d \) in the datasheet
- \( I_{\text{T}(AV)} \) is the average on-state current
- \( I_{\text{T}(RMS)} \) is the RMS on-state current

*Figure 1* shows the RMS and average values for different waveforms of current.
1.1.3 Dissipated power in a TRIAC

A TRIAC is made up of two thyristors connected back to back. This means we consider the sum of the dissipated power of both thyristors.

The following formula gives the total dissipated power versus $I_{T(RMS)}$ current through the TRIAC (see Figure 1 C with $t_0 = 0$):

$$P = \frac{2 \cdot \sqrt{2}}{\pi} \cdot I_{T(RMS)} \cdot V_{t0} + R_d \cdot I_{T(RMS)}^2$$

For a phase angle conduction the RMS current is given in Figure 1 C.

1.1.4 TRIAC without external heatsink

*Figure 2* shows the thermal equivalent diagram for a TRIAC without external heatsink.

In practice the imposed parameters are:
- $T_a$: ambient air temperature where the TRIAC is located
- $R_{th(j-a)}$: thermal resistance between junction and ambient air given in the datasheet
- $P$: dissipated power in the TRIAC depending on the used TRIAC and on the load current

The following equation defines the junction temperature depending on these parameters:

$$T_j = P \cdot R_{th(j-a)} + T_a$$
1.1.5 TRIAC with external heatsink

If the estimated junction temperature is higher than the maximum junction temperature specified in the datasheet, a heatsink has to be used.

Recommendation: this calculation has to be made in the worst case scenario i.e with the maximum dissipated power, load and line voltage dispersions. We have to consider the maximum ambient temperature around the component i.e. inside the box where the TRIAC is located.

The same approach as presented in the previous section allows a suitable heatsink to be defined. Figure 3 shows the thermal equivalent diagram.

Figure 2. Thermal equivalent diagram

![THERMAL_EQUIVALENT_DIAGRAM](image)

Figure 3. Thermal equivalent diagram with external heatsink

![THERMAL_EQUIVALENT_DIAGRAM_WITH_HEATSINK](image)
The formula to calculate the thermal resistance between heatsink and ambient air is the following:

\[
R_{\text{th(h-a)}} = \frac{T_j - T_a}{P} - R_{\text{th(j-c)}} - R_{\text{th(c-h)}}
\]

Where:
- \(T_j\) is the junction temperature in °C
- \(P\) is the maximum dissipated power in W
- \(R_{\text{th(j-c)}}\) is the thermal resistance between junction and case in °C/W
- \(R_{\text{th(c-h)}}\) is the thermal resistance between case and heatsink in °C/W, depending on the contact case/heatsink.

Since the current alternates in a TRIAC, we have to consider the \(R_{\text{th(j-c)}}\) in alternating current which is different to the \(R_{\text{th(j-c)}}\) in direct current.

This difference is due to the die of the TRIAC. The first half of the silicon die works when the current is positive, the second when the current is negative. Because of the thermal coupling between these two parts, this gives the following equation.

\[
R_{\text{th(j-c)}}^{AC} = 0.75 \cdot R_{\text{th(j-c)}}^{DC}
\]

1.1.6 Choice of heatsink

Choosing a heatsink depends on several parameters; the thermal characteristic, the shape and the cost.

However, in some applications a flat heatsink can be sufficient. Figure 4 shows the curve \(R_{\text{th(h-a)}}\) versus the length of a flat square heatsink for different materials and thickness.

Some applications need heatsinks with an optimized shape where the thermal resistances are not known.

For this, the best solution involves measuring the case temperature of the component in the worst case scenario and keeping to the following formula:

\[
T_c < T_{\text{max}} - P \cdot R_{\text{th(j-c)}}
\]

Where:
- \(T_c\) is the case temperature
- \(T_{\text{max}}\) is the maximum junction temperature
- \(P\) is the dissipated power in the component
- \(R_{\text{th(j-c)}}\) is the thermal resistance between junction and case.
1.1.7 Forced cooling

For high power or very high power applications, a forced-air or liquid cooling heatsink may be required. Heatsink manufacturers give a coefficient depending on the air or liquid flow. However, in some applications like vacuum cleaners, dissipated power is only a few watts and air flow cooling is available. This allows a very small heatsink to be used, very often a flat aluminium heatsink. In this case it is necessary to measure the case temperature in the worst case scenario and to check the following formula:

\[ T_c < T_{j\text{max}} - P \cdot R_{th(j-c)} \]

1.2 Thermal impedance

In steady state, a thermal equivalent circuit can be made only with thermal resistances. However, for pulse operation it can be useful to consider the thermal impedance, especially when the component is on during a time lower than the time to reach the thermal resistance. The thermal impedance value versus pulse duration is given in the datasheets (see an example in Figure 5), in the form of the relationship \( Z_{th}/R_{th} \) plotted against pulse duration.

For example, BTA08-600SW is able to dissipate \( \approx 27 \) W without heatsink during 1 s:

\[ P = \frac{T_{j\text{max}} - T_{\text{ambient}}}{Z_{th(j-a)} (1 \text{ s})} \]

\( Z_{th(j-a)} \) can be obtained from the datasheet by reading the value of the ratio \( Z_{th}/R_{th} \) from the curve (in the case of this product the ratio is 0.06 as seen in Figure 5) and multiplying the ratio by the value of \( R_{th(j-a)} \) from the datasheet. For this example \( R_{th(j-a)} \) is 60 °C/W

\[ P = \frac{125 - 25}{60 \times 0.06} = 27.5 \text{ W} \]
In steady state, with the same ambient temperature, the same TRIAC is able to dissipate:

\[
P = \frac{125 - 25}{60} = 1.7 \text{ W}
\]

**Figure 5.** Thermal transient impedance of a BTA08-600SW.

1.3 **Insulating materials**

We can classify them in 3 types as following:

**Mica insulators**

This has been the most commonly used insulator for many years. Its insulating quality is good, but due to its rigidity the thermal interface is not very good, and needs contact grease on both sides. Because of its rigidity it can be easily broken.

**Ceramic insulators**

More expensive than mica, their thermal resistances are lower. Due to their rigidity, they also need contact grease. However, they can be easily broken, as they are less fragile than mica.

**Silicone insulators**

These materials are not rigid and therefore do not need contact grease. They assume the shape of the component and of the heatsink if sufficient pressure is applied. The problems previously explained disappear. According to manufacturers, the stability in time is much better than with contact grease. However the thermal resistance is higher than the combination of the mica + grease.
Table 1. $R_{th(c-h)}$ for different materials for TO-220AB package

<table>
<thead>
<tr>
<th>Material</th>
<th>$R_{th(c-h)}$ °C</th>
</tr>
</thead>
<tbody>
<tr>
<td>Contact grease</td>
<td>0.5</td>
</tr>
<tr>
<td>Mica + grease thickness = 80 µm</td>
<td>1.7</td>
</tr>
<tr>
<td>Mica dry thickness = 80 µm</td>
<td>4</td>
</tr>
<tr>
<td>Silicone insulator</td>
<td>2.6</td>
</tr>
</tbody>
</table>

Table 1 shows the thermal resistance for different TO-220AB insulators and for a given pressure ($F = 30$ N).

### 1.4 Insulated components

Most of the thyristors and TRIACs manufactured by STMicroelectronics are available in insulated and non-insulated packages. For insulated packages, insulation can be achieved in two different ways:

- ceramic between the die pad and the heatsink of the component (TO-220AB / TOP3 / RD91 packages)
- resin used for encapsulation (ISOWATT220AB / TO-220FPAB packages)

All insulated packages delivered by STMicroelectronics are in accordance with UL1557 recognition applicable for “electrically isolated semiconductors”. The added material increases the thermal resistance between the junction and the case, but the total thermal resistance ($R_{th(j-a)}$) is lower than the one when using a non insulated component with an external insulating material. In addition, it simplifies assembly and reduces the cost.

For two 16 A TRIACs in TO-220AB package, $R_{th(j-c)}\text{AC}$ values (°C/W) are shown in Table 2:

<table>
<thead>
<tr>
<th>BTA16-600C (insulated version)</th>
<th>BTB16-600C (non-insulated version)</th>
</tr>
</thead>
<tbody>
<tr>
<td>2.1 device</td>
<td>1.2 device</td>
</tr>
<tr>
<td>+ 0.5 grease</td>
<td>+ 1.7 mica + grease</td>
</tr>
<tr>
<td>= 2.6 total</td>
<td>= 2.9 total</td>
</tr>
</tbody>
</table>

### 1.5 Handling and mounting techniques

The use of inappropriate techniques or unsuitable tools during handling and mounting can affect the long term reliability of the device, or even damage it.

#### 1.5.1 Bending and cutting leads

Lead bending must be done carefully. The lead must be firmly held between the plastic package and the bending point during lead operation. If the package / lead interface is strained, the resistance to humidity is impaired and in addition mechanical stress is inflicted on the die. This damage can affect the long term reliability of the devices.
There are six basic rules to bear in mind:

1. Never clamp the plastic package (*Figure 6*).

   **Figure 6. Clamping the lead not the package**

   ![Diagram showing correct and incorrect clamping methods](image)

2. Clamp the leads firmly between the plastic package and the bend / cut point (*Figure 7*).

   **Figure 7. Clamping the lead between the package and the bend / cut point**

   ![Diagram showing correct and incorrect clamping methods](image)

3. Bend the leads at least 3 mm from the plastic package (*Figure 8*).

   **Figure 8. Bending the lead at least 3 mm from the plastic package**

   ![Diagram showing correct and incorrect bending methods](image)
4. Never bend the leads laterally (Figure 9).

Figure 9. Bending the leads laterally (not allowed)

5. Never bend the leads more than 90° and never bend more than once.

6. Make sure that the bending / cutting tool does not damage the leads.

1.5.2 Using a heatsink

Mounting surface preparation

- The mounting surface should be flat, clean and free of burrs and scratches.
- The use of a thin layer of thermal silicone grease ensures a very low contact thermal resistance between the component and the heatsink. An excessively thick layer or a excessively viscous silicone grease may have the opposite effect and cause the deformation of the tab.
- The planarity of the contact surface between device and heatsink must be very low (less than 50 µm for TO-220AB).

Insertion

If the heatsink is mounted on the PC board, it should be attached to the component before the soldering process of the leads.

Mounting techniques

Mounting must be done carefully. Excessive stress may induce distortion of the tab and as a consequence mechanical damage on the die.

Soldering: It is not recommended for through-hole packages.
**With rivets:** Pop rivets should never be used for the following reasons:

- A too rigorous expansion of the metal can lead to a distortion of the heatsink hole and induce mechanical stresses on the die.
- High crimping shock can damage the die.

Press rivets can be used with caution provided they are of a soft metal like aluminium. The crimping force must be applied slowly and carefully in order to avoid shock and deformation of the heatsink.

**Figure 10. Assembly with rivet**

**With clips:** Care should be taken with the contact area between the plastic case and the clip: the maximum pressure allowed on plastic is 150 N/mm². Over this value, cracks may be induced in the package. Therefore, the clips have to be round or smooth in the contact area to avoid concentrated loads on the plastic body. The force applied on the component depends on the heatsink and the component thickness, so they must be specially designed to take this value into account. Screw assembly is preferred to clip assembly for insulated packages.

**Figure 11. Clip assembly**
**With screws:** The following precautionary measures should be taken:
- To avoid tab distortion, a rectangular washer must be put between the screw head and the tab, and a compression washer must be put between the tab and the nut.

**Figure 12. Correct assembly**

- Take care to avoid mechanical shock during screwing.
- Keep the screw straight.
- Appropriate screwing torque should be used, excessive screwing torque may cause the distortion of the tab and induce bad thermal contact. In addition it can generate cracks in the die.

**Figure 13. Incorrect assembly**

The thermal contact resistance depends on the force generated by the applied torque on the screw:

$$ F = \frac{2 \cdot T \cdot \pi}{P + r \cdot D \cdot \pi} $$

Where:
- $T$ is applied torque on the screw in N.m
- $P$ is pitch in m
- $D$ is screw diameter in m
- $r$ is rubbing factor: # 0.12 for steel-steel with grease and # 0.2 for steel-aluminium

The relative variation of the $R_{th(c-h)}$ compared with the value of $R_{th(c-h)}$ at 0.6 Nm versus the torque for an M3 screw used for the TO220AB is given in Figure 14.
Table 3. Recommended torque and thermal contact resistance

<table>
<thead>
<tr>
<th>Package</th>
<th>Torque (Nm)</th>
<th>Thermal contact resistance (°C/W)</th>
</tr>
</thead>
<tbody>
<tr>
<td>TO-220AB / PENTAWATT</td>
<td>0.4 to 0.6</td>
<td>0.5</td>
</tr>
<tr>
<td>ISOWATT220 / TO-220FPAB</td>
<td>0.4 to 0.6</td>
<td>0.5</td>
</tr>
<tr>
<td>TOP3 / TOP3I</td>
<td>0.9 to 1.2</td>
<td>0.1</td>
</tr>
<tr>
<td>RD91</td>
<td>0.9 to 1.2</td>
<td>0.1</td>
</tr>
</tbody>
</table>

1. For BTB20-xxx, BTB24-xxx and TYNxx40, the maximum torque is 0.5 Nm.
1.6 Through-hole package wave soldering

The lead-free through-hole devices may be soldered with lead-free solder pastes or alloys (Sn-Ag-Cu based alloys). The typical soldering temperature is 260 °C.

Alternatively these devices may be soldered with SnPb based solder pastes. The soldering temperature is then typically around 220 °C.

Interface adherences on through-hole package structures are qualified to sustain only 3 consecutive dips of their connections in a solder pot at 260 °C (-0 °C / +5 °C).

- immersion duration: 10 seconds each
- delay between 2 dippings: 5 minutes
- minimum distance solder to package plastic body: according to packages, by default 1 mm

Lead-free devices are described in an internal specification defining:

- their characteristics: lead-free connection coating, solderability and identification features
- their reliability such as soldering resistance, reliability performances, whiskers risk prevention.

This specification is available for ST customers upon request (Title: ECOPACK® Components Definition & Characteristics). Please consult that document for further information.

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2 Surface mount packages

2.1 Thermal resistance

The thermal resistance of a semiconductor device characterizes the device’s capability to dissipate the heat generated by the chip during operation. This parameter allows us to calculate the junction temperature, taking into account the device environment (load current, ambient temperature, mounting conditions etc...).

For surface mounted devices (SMDs), the thermal resistance between junction and ambient, called \( R_{\text{th}(j-a)} \), depends on the copper surface used under the tab. Figure 15 shows curves giving the relation between \( R_{\text{th}(j-a)} \) and the copper surface under the tab for an FR4 board - 35 µm copper thickness.

Figure 15. \( R_{\text{th}(j-a)} \) versus copper surface under tabs (FR4 board - copper thickness = 35 µm) for several typical packages

2.2 Thermal impedance

When dealing with short duration pulses, the thermal impedance must be considered to calculate the junction temperature. Depending on the time scale, the following elements are thermally prevalent:

- \( t_p < 10 \text{ ms} \): die influence
- \( t_p < 0.1 \text{ s} \): package influence
- \( t_p < 10 \text{ s} \): PCB influence
- above 10 s: thermal exchange board-air (example: with / without forced cooling)

Figure 16 shows the \( Z_{\text{th}} / R_{\text{th}} \) ratio for SMD packages and Figure 17 shows \( Z_{\text{th}(j-a)} \) for DPAK and \( D^2 \text{PAK} \).
2.3 Mounting techniques and $R_{th(j-a)}$

$R_{th(j-a)}$ varies with the printed circuit board technology. Different technologies can be used depending on the performance required in the design. Four techniques are commonly used:

- FR4 - Copper
- IMS (Insulated Metal Substrate)
- FR4 board with copper filled through holes + HEATSINK
- IMS + HEATSINK.
As the FR4 board is commonly used in surface mounting techniques, there are several ways of overcoming its low thermal performance:

- use of large heat spreader areas (heat sink) at the copper layer of the PCB
- use of copper-filled through holes in addition to an external heatsink for an even better thermal management

However, due to its power dissipation limitation, using the FR4 board with these techniques is advisable only for currents up to 8 A max.

A technology available today is Insulated Metallic Substrate (IMS). This offers greatly enhanced thermal characteristics for surface mount components. IMS is a substrate consisting of three different layers:

- base material which is available as an aluminum or a copper plate
- thermal conductive dielectric layer
- copper foil, which can be etched as a circuit layer.

Even if a higher power is to be dissipated, an external heatsink can be applied leading to an \( R_{th(j-a)} \) of 4.5 °C/W (see Table 4). This is commonly applied in practice, leading to reasonable heatsink dimensions. Often, power devices are defined by considering the maximum junction temperature of the device. In practice, however, this is far from being fully exploited.

The designer should carefully consider which is appropriate mounting method (see Table 4) to be used according to the dissipated power. The type of board will influence the thermal performance of the system. Table 4 shows the \( R_{th(j-a)} \) depending on the mounting techniques for DPAK and D²PAK.
The surface mount assembly is a 4-step process.
1. solder paste printing
2. component placement on the board
3. reflow soldering
4. cleaning (optional)

The soldering process causes considerable thermal stress to a semiconductor component. This has to be minimized to assure a reliable and extended lifetime of the device. SOT-23, SOT-223, SO-8 and DPAK packages can be exposed to a maximum temperature of 260 °C for 10 to 30 seconds. For the D²PAK package the maximum temperature is 245 °C.

Overheating during the reflow soldering process may damage the device, therefore any solder temperature profile should be within these limits. Reflow techniques are most common in surface mounting. Typical heating profiles for leadfree solder (ST ECOPACK) are given in Figure 19 for small packages (SOT-23, SOT-223, DPAK), either for mounting on a FR4 or on metal-backed boards (IMS). Please refer to the IPC/JEDEC J-STD-020C standard for further information about “small” and “large” component definitions.

Note: Soldering profile defined in IPC/JEDEC J-STD-020C standard is used for reliability assessment and typically describes warmest profiles used for component mounting, not the necessary temperatures to achieve good soldering.

Wave soldering is not advisable for DPAK and D²PAK because it is almost impossible to contact the whole package slug during the process.

### Table 4. $R_{th(j-a)}$ for DPAK and D²PAK according to mounting method

<table>
<thead>
<tr>
<th>Mounting method</th>
<th>DPAK (°C/W)</th>
<th>D²PAK (°C/W)</th>
</tr>
</thead>
<tbody>
<tr>
<td>FR4</td>
<td>70</td>
<td>50</td>
</tr>
<tr>
<td>FR4 with 10 cm² heatsink on board</td>
<td>40</td>
<td>35</td>
</tr>
<tr>
<td>FR4 with copper filled holes and external heatsink</td>
<td>13</td>
<td>12</td>
</tr>
<tr>
<td>IMS (40 cm²) in free air</td>
<td>9</td>
<td>8</td>
</tr>
<tr>
<td>IMS with external heatsink</td>
<td>4.5</td>
<td>3.5</td>
</tr>
</tbody>
</table>
For each individual board, the appropriate heat profile has to be adjusted experimentally. The current proposal is just a starting point. In every case, the following precautions have to be considered:

- Always preheat the device. The purpose of this step is to minimize the rate of temperature rise to less than 3 °C per second (recommended 2 °C/s) to minimize the thermal shock on the component.
- Dryout section, after preheating, ensures that the solder paste is fully dried before starting reflow step. Also, this step allows the temperature gradient on the board to be evened out.
- Peak temperature should be at least 30 °C higher than the melting point of the solder alloy chosen to ensure the reflow quality. In any case the peak temperature should not exceed 260 °C.

Lead-free devices are described in an internal specification defining:

- their characteristics: lead-free connection coating, solderability and identification features
- their reliability such as soldering resistance, reliability performances, whiskers risk prevention.

This specification is available for ST customers upon request (Title: ECOPACK Components Definition & Characteristics). Please consult that document for further information about reflow and wave soldering.

Voids pose a difficult reliability problem for large surface mount devices. Such voids under the package result in poor thermal contact and the high thermal resistance leads to component failures.

Coplanarity between the substrate and the package can be easily verified. The quality of the solder joints is very important for two reasons:

- Poor quality solder joints directly result in poor reliability.
- Solder thickness affects the thermal resistance significantly. Thus, tight control of this parameter results in thermally efficient and reliable solder joints.
3 Revision history

Table 5. Revision history

<table>
<thead>
<tr>
<th>Date</th>
<th>Revision</th>
<th>Changes</th>
</tr>
</thead>
<tbody>
<tr>
<td>Nov-1997</td>
<td>1</td>
<td>Initial release.</td>
</tr>
<tr>
<td>Oct-2000</td>
<td>2</td>
<td>Latest update</td>
</tr>
</tbody>
</table>
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